

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12680	(carbon adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:12
L2	3578	diamond near10 (carbon adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:12
L3	493	diamond near10 (carbon adj film) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:12
L4	16	diamond near10 (carbon adj film) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:12
L5	16	(diamond near10 (carbon adj film)) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:13
L6	3	(diamond near10 (carbon adj film)) with (tft or (thin adj film adj transistor)) and takeshi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:15
L7	10	(diamond near10 (carbon adj film)) with (tft or (thin adj film adj transistor)) with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:15
L8	2	(diamond near10 (carbon adj film)) with (tft or (thin adj film adj transistor)) with substrate with (insulating or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:16
L9	10834	(tft or (thin adj film adj transistor)) with substrate with (insulating or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:16

L10	3	(tft or (thin adj film adj transistor)) with substrate with (insulating or dielectric) with carbon with diamond	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:17
L11	9402	(diamond near like near carbon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:17
L12	1726	(diamond near like near carbon). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:17
L13	108	(diamond near like near carbon). clm. and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:17
L14	37	(diamond near like near carbon). clm. and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:18
L15	0	(back or rear) near surface near (diamond near like near carbon). clm. and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:18
L16	0	(back or rear) near surface near substrate near (diamond near like near carbon).clm. and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:18
L17	1	(back or rear) near5 surface near5 substrate near5 (diamond near like near carbon).clm. and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:18
L18	4	(back or rear) near5 surface near5 substrate near5 (diamond near like near carbon) and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:20
L19	11	(back or rear) near5 surface near5 substrate near5 (diamond near like near carbon) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:20

L20	15	(back or rear) near5 surface near5 substrate near5 (carbon) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:21
L21	1899	(carbon near2 film).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:21
L22	112	(carbon near2 film).clm. and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:21
L23	58	(carbon near2 film).clm. and (tft or (thin adj film adj transistor)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:21
L24	9	(carbon near2 film).clm. with (tft or (thin adj film adj transistor)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:23
L25	5	(carbon near2 film).clm. with (tft or (thin adj film adj transistor)). clm. and diamond	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:24
L26	5	(carbon near2 film) with (tft or (thin adj film adj transistor)).clm. and diamond	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:24
L27	39	(carbon near2 film) with (tft or (thin adj film adj transistor)) and diamond	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:28
L28	21	(carbon near2 film) with (tft or (thin adj film adj transistor)) with diamond	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:25
L29	15	(carbon near2 film) with (tft or (thin adj film adj transistor)) with diamond with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:25

L30	21	(carbon near2 film) with (tft or (thin adj film adj transistor)) and (diamond or dlc) near10 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:29
L31	18	(carbon near2 film) with (tft or (thin adj film adj transistor)) and (diamond or dlc) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:29
L32	4903	(diamond or dlc) near10 surface near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:30
L33	112	(diamond or dlc) near10 surface near10 substrate near10 insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:30
L34	7	((diamond or dlc) near10 surface near10 substrate near10 insulating) with (tft or (thin adj film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:31
L35	2	((diamond or dlc) near10 surface near10 substrate near10 insulating) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:31
L36	8	((diamond or dlc) near10 surface near10 substrate) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:32
L37	19	((diamond or dlc) near10 surface) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:33
L38	71	((diamond or dlc)) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:33
L39	32	((diamond near2 carbon) or dlc) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:35

L40	2272	((((diamond near2 carbon) or dlc)) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:35
L41	341	(((((diamond near2 carbon) or dlc)) near10 substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:35
L42	5	(((((diamond near2 carbon) or dlc)) near10 substrate).clm. and ((tft or (thin adj film adj transistor)) near10 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:36
L43	3	(((((diamond near2 carbon) or dlc)) near10 substrate).clm. and ((tft or (thin adj film adj transistor)) near10 substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:36
L44	28	(((((diamond near2 carbon) or dlc))) .clm. and ((tft or (thin adj film adj transistor)) near10 substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:36
L45	51	(((((diamond near2 carbon) or dlc))) .clm. and ((tft or (thin adj film adj transistor))) .clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:39
L46	486	(((((diamond near2 carbon) or dlc))) near10 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:39
L47	486	(((((diamond near2 carbon) or dlc))) near10 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:39
L48	116	(((((diamond near2 carbon) or dlc))) near10 surface near10 substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:39
L49	2	(((((diamond near2 carbon) or dlc))) near10 surface near10 substrate).clm. and (tft or (thin adj film adj transistor)) .clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:40

L50	51	(((((diamond near2 carbon) or dlc))) near10 surface near10 substrate) and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:40
L51	139	(((((diamond near2 carbon) or dlc))) near10 surface near10 substrate) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:40
L52	6	(((((diamond near2 carbon) or dlc))) near10 surface near10 substrate) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:45
L53	7	(((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:46
L54	185	(((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:46
L55	18	(((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) and (tft or (thin adj film adj transistor))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:47
L56	185	(((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) and (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:47
L57	7	(((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) with (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:48
L58	29	(((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) same (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:48
L59	3	(((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) same (tft or (thin adj film adj transistor))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:48

L60	29	((((((diamond near2 carbon) or dlc))) near10 (insulating or dielectric)) same (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 01:48
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